

B1
end

comprises a gate electrode 11, a gate insulator 35, a semiconductor layer, a ohmic contact layer, a source electrode, a drain electrode, etc.

Page 9, between lines 8 and 13, please delete the one paragraph and replace therefore with the following one paragraph.

B2

And, on the second substrate 33, a light shielding layer 25 is formed to shield light leakage from the gate bus line 1, data bus line, and TFT. A color filter layer 23 is on light shielding layer 25. A common electrode 17 is on color filter layer 23. And a liquid crystal layer is between the first an second substrates 31 and 33.

Pages 10-11, between page 10, line 11 and page 11, line 16 please delete the current four paragraphs and replace therefor with the following four paragraphs.

B3

To manufacture the LCD, in each pixel region on the first substrate 31, a TFT is formed comprising a gate electrode, a gate insulator 35, a semiconductor layer, an ohmic contact layer and source/drain electrodes. At this time, a plurality of gate bus lines 1 and a plurality of data bus lines are formed to divide the first substrate 31 into a plurality of pixel regions.

The gate electrode and the gate bus line 1 are formed by sputtering and patterning a metal such as Al, Mo, Cr, Ta, or Al alloy, the combination of the metals etc. The gate insulator 35 is formed by depositing SiN_x or SiO_x using PECVD (Plasma Enhancement Chemical Vapor Deposition) thereon.

The semiconductor layer 5 and the ohmic contact layer are formed by depositing with PECVD, and patterning amorphous silicon (a-Si) and doped amorphous silicon (n^+ a-Si), respectively. Also, the gate insulator 35 can be formed by depositing SiN_x , SiO_x , a-Si and n^+ a-Si continuously, and then the semiconductor layer and the ohmic contact layer can be formed by patterning a-Si and n^+ a-Si. Further the gate insulator 35 can be formed with BCB (BenzoCycloButene), acrylic resin or polyimide based material so as to improve